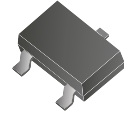


CDST116-G

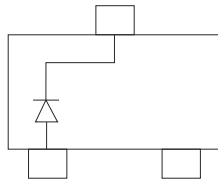
RoHS Device



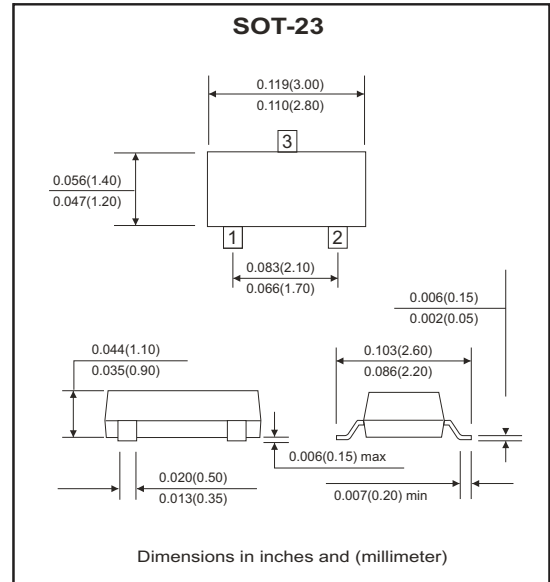
Features

- Low leakage current applications.
- Medium speed switching times.

Polarity:



Marking: JV



Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V_{RRM} V_{RWM} V_R	75	V
Forward continuous current	I_{FM}	215	mA
Power dissipation	P_D	250	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ.	Max	Unit
Reverse breakdown voltage	$I_R=100\mu A$	$V_{(BR)R}$	75			V
Forward voltage	$I_F=1mA$	V_{F1}			0.9	V
	$I_F=10mA$	V_{F2}			1	V
	$I_F=50mA$	V_{F3}			1.1	V
	$I_F=150mA$	V_{F4}			1.25	V
Reverse current	$V_R=75V$	I_R			5	μA
Capacitance between terminals	$V_R=0V, f=1MHz$	C_T		2		pF
Reverse recovery time	$I_F=I_R=10mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$	t_{rr}			3	nS

RATING AND CHARACTERISTIC CURVES (CDST116-G)

Fig.1 - Forward Current Derating Curve

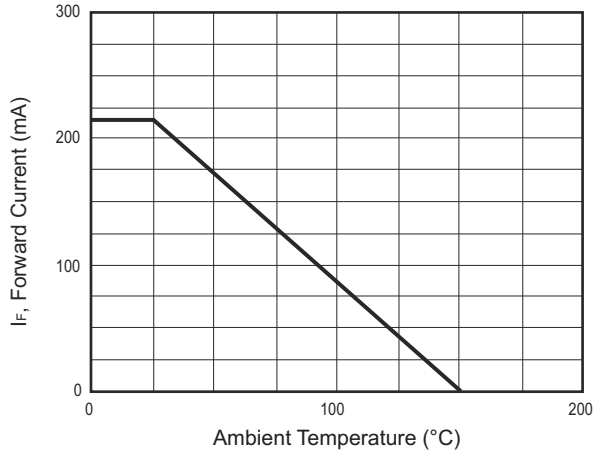


Fig.2 - Forward Voltage Characteristics

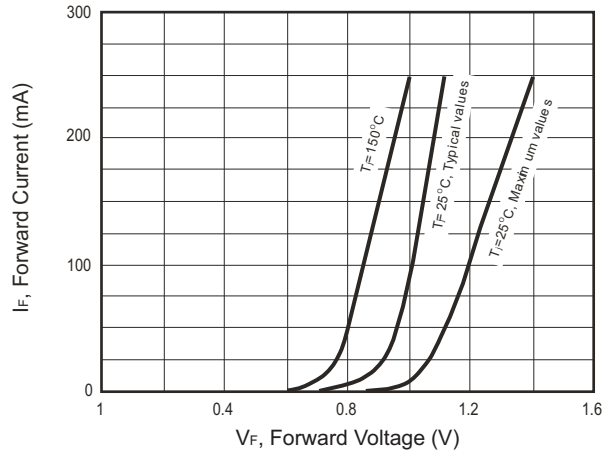


Fig.3 - Reverse Characteristics

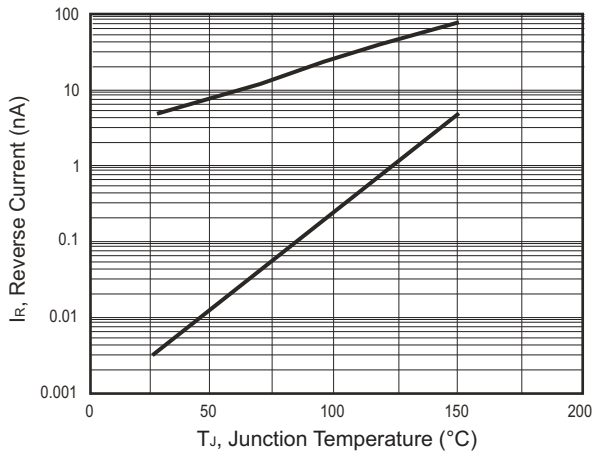


Fig.4 - Diode Capacitance Characteristics

